

isc Silicon NPN Darlington Power Transistor

2SD837

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 1000(\text{Min.}) @ I_C = 3A$
- High Switching Speed

APPLICATIONS

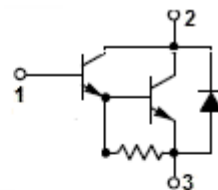
- Audio power amplifiers
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

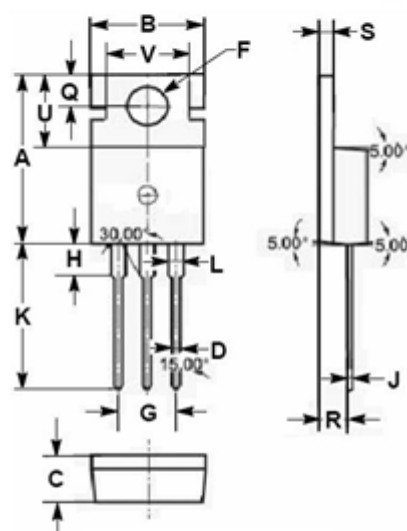
SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_{CM}	Base Current-Peak	8	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



1 2 3



PIN 1. BASE
2. COLLECTOR
3. EMITTER
TO-220C package



DIM	mm	
	MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

isc Silicon NPN Darlington Power Transistor**2SD837****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 30mA ; I _B = 0	60			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 12mA			2	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 20mA			4	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 3A ; V _{CE} = 3V			2.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 60V; I _E = 0			0.2	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = 30V; I _B = 0			0.5	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C =0			2	μ A
h _{FE-1}	DC Current Gain	I _C = 0.5A ; V _{CE} = 3V	1000			
h _{FE-2}	DC Current Gain	I _C = 3A ; V _{CE} = 3V	1000		10000	

Switching Times

t _{on}	Turn-On Time	I _C = 3A; I _{B1} = -I _{B2} = 12mA		0.3		μ s
t _{off}	Turn-Off Time			4		μ s